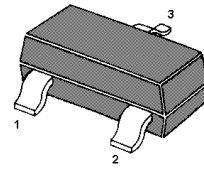


NPN Silicon Epitaxial Planar Transistor
for RF amplifier.

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 +150	$^\circ\text{C}$

Characteristics at $T_{amb}=25\text{ }^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$ Current Gain Group	R	h_{FE}	40	-	80	-
	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
Collector Emitter Saturation Voltage at $I_C=10\text{mA}$, $I_B=1\text{mA}$	$V_{CE(sat)}$	-	-	0.3	V	
Collector Cutoff Current at $V_{CB}=30\text{V}$	I_{CBO}	-	-	0.5	μA	
Emitter Cutoff Current at $V_{EB}=4\text{V}$	I_{EBO}	-	-	0.5	μA	
Collector Base Breakdown Voltage at $I_C=10\mu\text{A}$	$V_{(BR)CBO}$	30			V	
Collector Emitter Breakdown Voltage at $I_C=5\text{mA}$	$V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $I_E=10\mu\text{A}$	$V_{(BR)EBO}$	4	-	-	V	
Transition Frequency at $V_{CE}=6\text{V}$, $I_E=-1\text{mA}$	f_T	-	550	-	MHz	
Output Capacitance at $V_{CB}=6\text{V}$, $f=1\text{MHz}$	C_{OB}	-	1.4	-	pF	

Electrical Characteristic Curves

Fig. 1 P_c-T_a

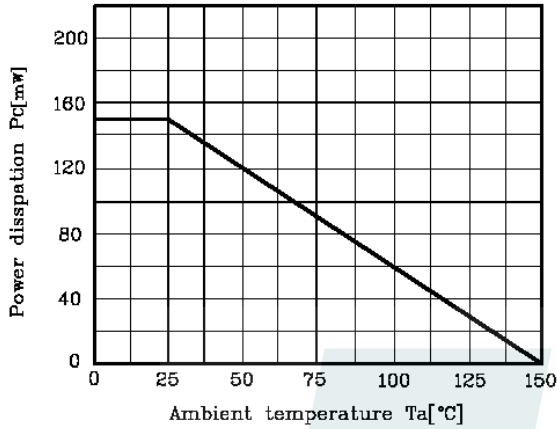


Fig. 2 I_c-V_{CE}

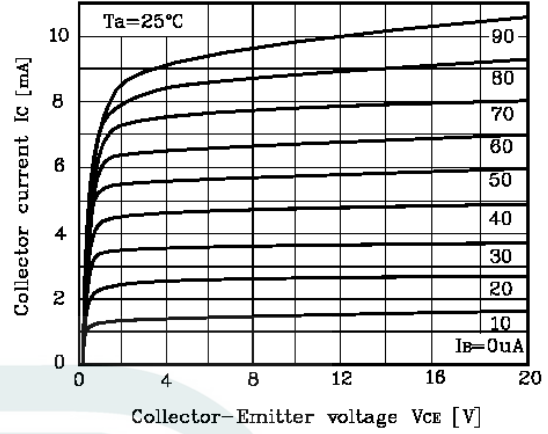


Fig. 3 $h_{FE}-I_c$

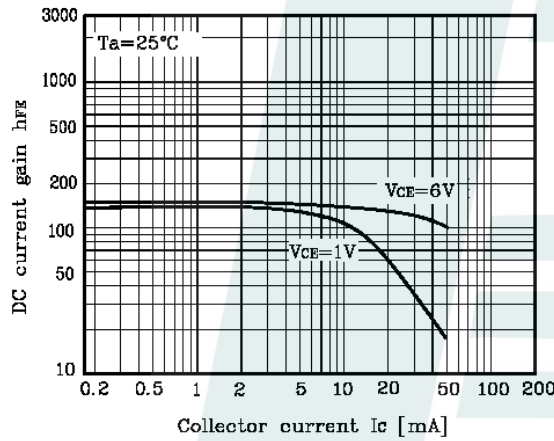


Fig. 4 f_T-I_E

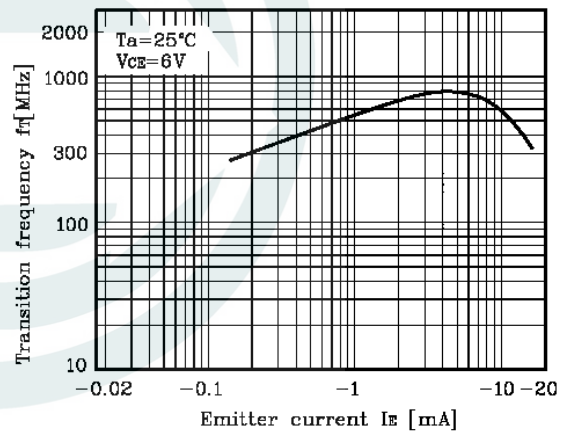


Fig. 5 $C_{ob}-V_{CB}, C_{ib}-V_{EB}$

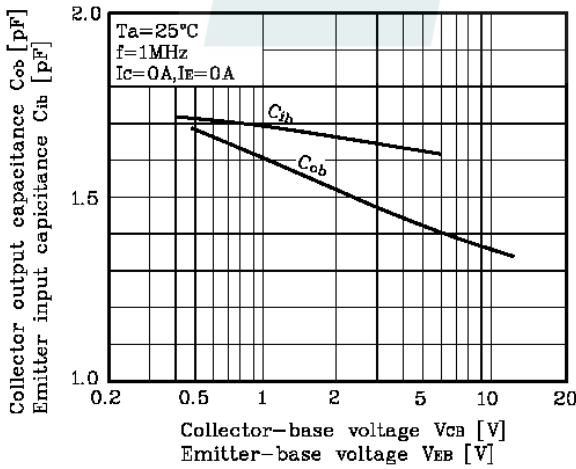
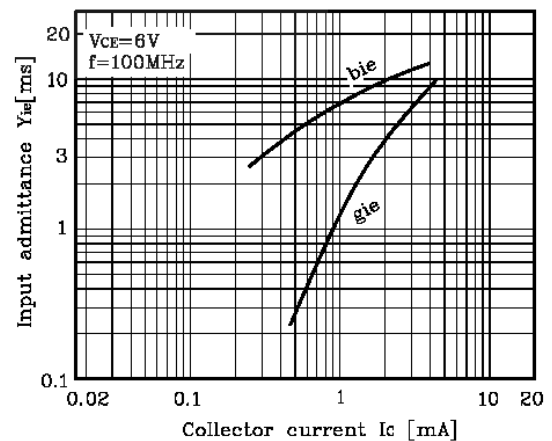


Fig. 6 $Y_{ie}-I_c$



Electrical Characteristic Curves

Fig. 7 I_C - Y_{oe}

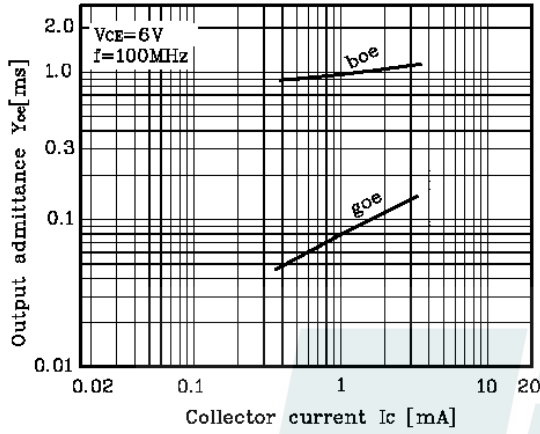


Fig. 8 I_C - Y_{fe}

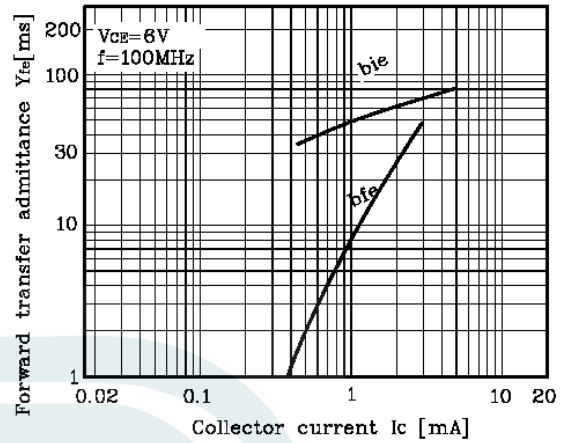


Fig. 9 I_C - Y_{re}

